

TMMDB3TG

DIAC

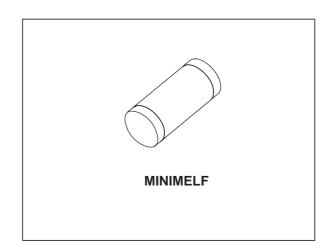
FEATURES

■ V_{BO}: 32V

Low breakover current: 15µA max
 Breakover voltage range: 30 to 34V

DESCRIPTION

Functioning as a trigger diode with a fixed voltage reference, the TMMDB3TG can be used in conjunction with triacs for simplified gate control circuits or as a starting element in fluorescent lamp ballasts.



ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter	Value	Unit
I _{TRM}	Repetitive peak on-state current tp = 20 μs F= 120 Hz	2	А
Tstg Tj	Storage temperature range Operating junction temperature range	- 40 to + 125	°C

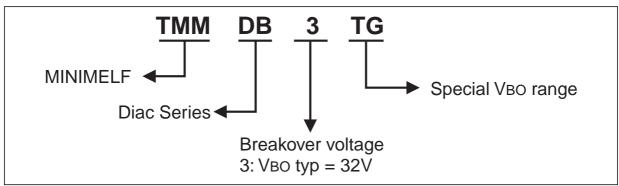
TMMDB3TG

ELECTRICAL CHARACTERISTICS (Tj = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions		Value	Unit
V _{BO}	Breakover voltage *	C = 22nF **	MIN.	30	V
			TYP.	32	
			MAX.	34	
I V _{BO1} - V _{BO2} I	Breakover voltage symmetry	C = 22nF **	MAX.	± 2	V
ΔV	Dynamic breakover voltage *	V _{BO} and V _F at 10mA	MIN.	9	V
Vo	Output voltage *	see diagram 2 (R=20Ω)	MIN.	5	V
I _{BO}	Breakover current *	C = 22nF **	MAX.	15	μА
tr	Rise time *	see diagram 3	MAX.	2	μs
I _R	Leakage current *	$V_R = 0.5 V_{BO} \text{ max}$	MAX.	10	μА

^{*} Applicable to both forward and reverse directions.

ORDERING INFORMATION



OTHER INFORMATION

Part Number	Marking	Weight	Base Quantity	Packing Mode
TMMDB3TG	(None)	0.04 g	2500	Tape & Reel

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^{**} Connected in parallel to the device.

Diagram 1: Voltage - current characteristic curve.

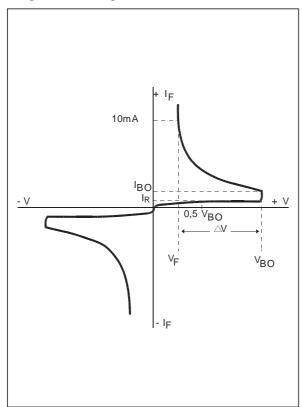


Diagram 2: Test circuit.

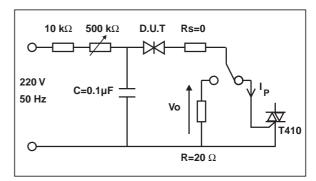


Diagram 3: Rise time measurement.

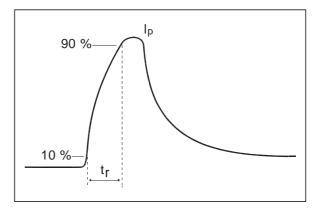


Fig. 1: Relative variation of VBO versus junction temperature (typical values)

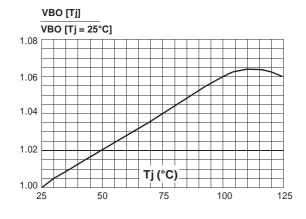


Fig. 2: Repetitive peak pulse current versus pulse duration (maximum values).

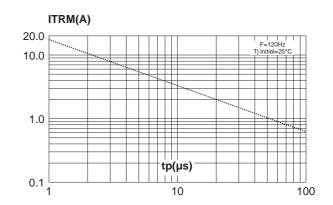
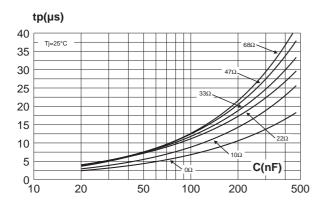
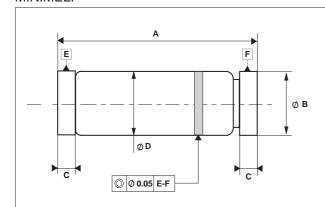


Fig. 3: Time duration while current pulse is higher 50mA versus C and Rs (typical values).

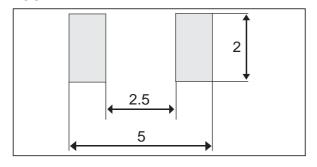


PACKAGE MECHANICAL DATA (in millimeters) **MINIMELF**



REF.	DIMENSIONS					
	Millimeters				Inches	,
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	3.30	3.40	3.6	0.130	0.134	0.142
В	1.59	1.60	1.62	0.063	0.063	0.064
С	0.40	0.45	0.50	0.016	0.018	0.020
D		1.50			0.059	

FOOTPRINT



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